



Docket No.: 050432-0657

**PATENT**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of	:	Customer Number: 20277
	:	
MARK T. RAMSBY, et al.	:	Confirmation Number: 9931
	:	
Application No.: 10/718,707	:	Group Art Unit: 2822
	:	
Filed: November 24, 2003	:	Examiner: Duong, Khanh B.
	:	
For: METHOD FOR FORMING NITROGEN-RICH REGIONS IN NON-VOLATILE SEMICONDUCTOR MEMORY DEVICES (AS TWICE AMENDED)		

**AMENDMENT**

Mail Stop Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

The following Amendment and Remarks are submitted in response to the Office Action dated May 4, 2005. Please amend the above-identified application as follows.